ABSTRACT

A semiconductor device includes: a stack including a first plane edge region, a second plane edge region, and a contact region located between the first plane edge region and the second plane edge region; and a first insulating structure including a first portion located in the first plane edge region of the stack, a second portion located in the second plane edge region of the stack, and a third portion located in the contact region of the stack, wherein the first portion includes a first curved edge.

FIG. 1B